TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL MOS TYPE

# GT40T101

#### HIGH POWER SWITCHING APPLICATIONS

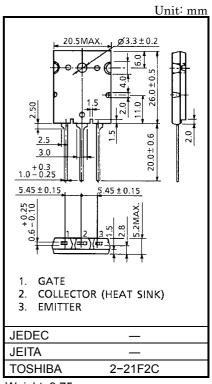
• Enhancement-Mode

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- High Speed  $: t_f = 0.4 \ \mu s (Max.) (I_C = 40 \ A)$
- Low Saturation  $: V_{CE} (sat) = 5.0 V (Max.) (I_C = 40 A)$

### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V <sub>CES</sub>	1500	V	
Gate-Emitter Voltage		V <sub>GES</sub>	±25	V	
Collector Current	DC	Ι <sub>C</sub>	40	A	
	1ms	I <sub>CP</sub>	80		
Collector Power Dissipation (Tc = 25°C)		P <sub>C</sub>	200	W	
Junction Temperature		Тj	150	°C	
Storage Temperature Range		T <sub>stg</sub>	-55~150	°C	

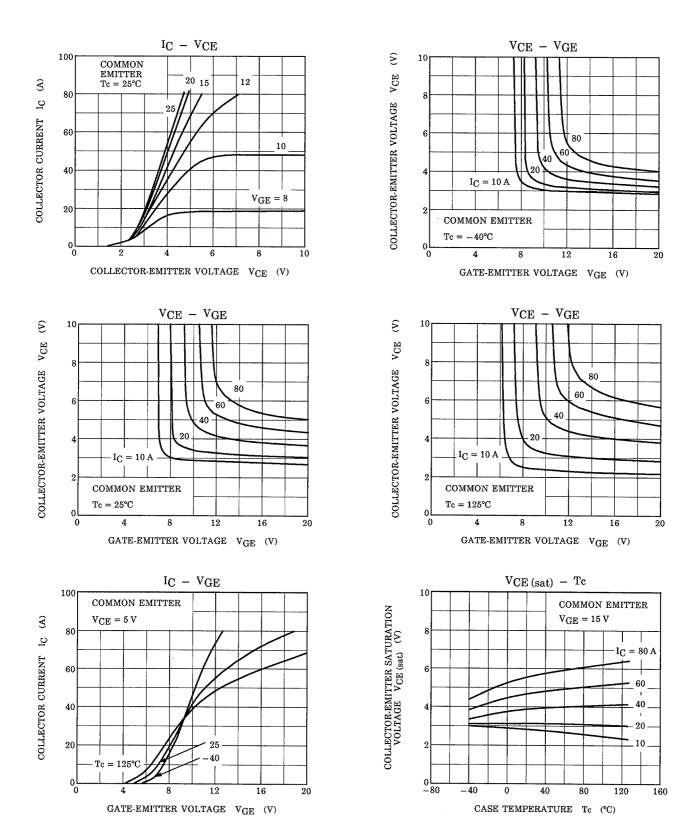


Weight: 9.75g

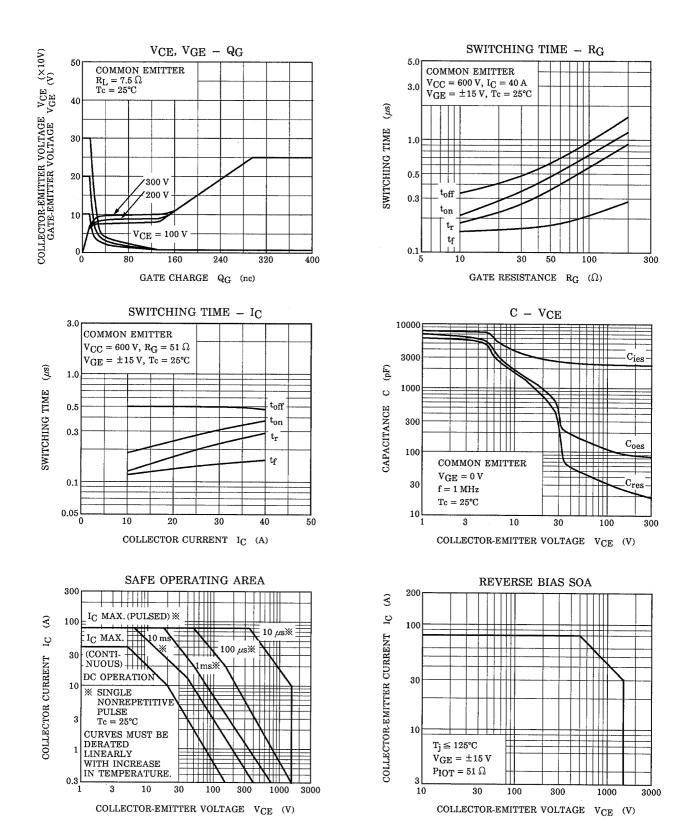
#### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

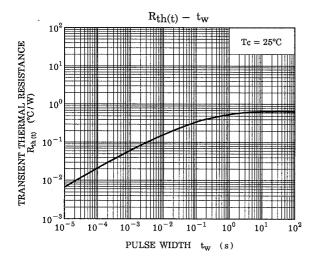
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Current		I <sub>GES</sub>	$V_{GE}$ = ±25 V, $V_{CE}$ = 0	_	_	±500	nA
Collector Cut-off C	urrent	ICES	V <sub>CE</sub> = 1500 V, V <sub>GE</sub> = 0	_	_	1.0	mA
Gate-Emitter Cut-o	off Voltage	V <sub>GE (OFF)</sub>	I <sub>C</sub> = 40 mA, V <sub>CE</sub> = 5 V	3.0	_	6.0	V
Collector-Emitter S	aturation Voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 40 A, V <sub>GE</sub> = 15 V	_	4.0	5.0	V
Input Capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1 MHz	-	3600	_	pF
Switching Time	Rise Time	tr	$ \begin{array}{c} 15 \text{ V} \\ 0 \end{array} \int_{-15 \text{ V}} 51 \Omega \\ V_{\text{CC}} = 600 \text{ V} \end{array} $		0.6	1.0	μs
	Turn-On Time	t <sub>on</sub>			0.7	1.1	
	Fall Time	t <sub>f</sub>		_	0.2	0.4	
	Turn-Off Time	t <sub>off</sub>		_	0.5	1.0	
Thermal Resistance	9	R <sub>th (j−c)</sub>	—	_	_	0.625	°C/W

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